

# APFDV303N 25V N-Channel Enhancement Mode MOSFET

## • General Description

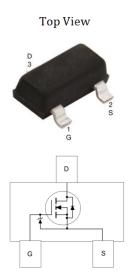
APFDV303N combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is designed especially for application in battery circuits using either one lithium or three cadmium or NMH cells. It can be used as an inverter or for high-efficiency miniature discrete DC/DC conversion in compact portable electronic devices like cellular phones or pagers. This device has excellent on-state resistance even at gate drive voltage as low as 2.5 volts.

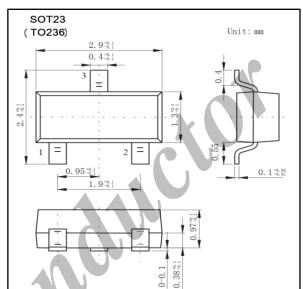
### Applications

- DC-DC converter for portable devices
- Load switch

## • Product Summary

 $\begin{array}{lll} V_{DS} & 25V \\ I_{D} \mbox{ (at $V_{GS} = 4.5V$)} & 0.68A \\ R_{DS(ON)} \mbox{ (at $V_{GS} = 4.5V$)} & <450 m\Omega \\ R_{DS(ON)} \mbox{ (at $V_{GS} = 2.7V$)} & <600 m\Omega \end{array}$ 







### Absolute Maximum Ratings Ta = 25°C

			1	
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{ extsf{DS}}$	25	V	
Gate-Source Voltage	$V_{GS}$	±8	V	
Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	ESD	6	kV	
Continuous Drain Current	$I_D$	0.68	A	
Pulsed Drain Current	$I_{DM}$	2		
Power Dissipation	$P_D$	0.35	W	
Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 to 150	°C	
Thermal Characteristics		·		
Thermal Resistance. Junction-to-Ambient	$R_{\theta JA}$	357	°C/W	



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#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D=250\mu A$ , $V_{GS}=0V$	25			V
Zero Gate Voltage Drain Current		$V_{DS}$ =20V, $V_{GS}$ =0V			1	μА
	$I_{DSS}$	$V_{DS}$ =20V, $V_{GS}$ =0V, $T_{J}$ =55°C		K	10	
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}$ =0V, $V_{GS}$ =±8V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	0.65		1.5	V
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =2.7V , V <sub>DS</sub> =5V	0.5			A
Static Drain-Source On-Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.5A			450	mΩ
	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, $I_D$ =0.5A, $T_J$ =125°C			800	
		$V_{GS}=2.7V$ , $I_{D}=0.2A$	7		600	
Forward Transconductance	$\mathbf{g}_{ ext{FS}}$	$V_{DS}$ =5V, $I_D$ =0.5A		1.45		S
Diode Forward Voltage	$V_{\text{SD}}$	$I_S=0.5A$ , $V_{GS}=0V$			1.2	V
Maximum Body-Diode Continuous Current	$I_S$				0.3	Α
Dynamic Parameters						
Input Capacitance	$C_{iss}$			50		
Output Capacitance	$C_{oss}$	$V_{GS}$ =0V, $V_{DS}$ =10V, f=1MHz		28		pF
Reverse Transfer Capacitance	$C_{rss}$			9		
Switching Parameters						
Total Gate Charge	$Q_{\mathrm{g}}$			1.64	2.3	
Gate Source Charge	$Q_{\rm gs}$	$V_{GS}$ =4.5V, $V_{DS}$ =5V, $I_{D}$ =0.5A		0.38		nC
Gate Drain Charge	$Q_{\mathrm{gd}}$			0.45		
Turn-On Delay Time	$t_{D(on)}$			3	6	
Turn-On Rise Time	t <sub>r</sub>	$V_{GS}$ =4.5V, $V_{DS}$ =6V,		8.5	18	
Turn-Off Delay Time	$t_{\mathrm{D(off)}}$	$I_D=0.5A$ , $R_{GEN}=50\Omega$		17	30	ns
Turn-Off Fall Time	$t_{\mathrm{f}}$			13	25	

### Ordering Information

Ordering Part Number	Package	MOQ
APFDV303N	SOT23 (TO236)	3,000 pcs / reel

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## • Typical Electrical and Thermal Characteristics

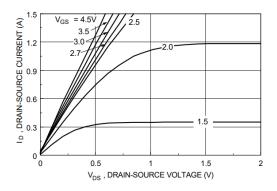


Figure 1. On-Region Characteristics.

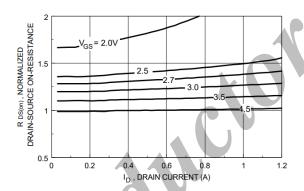


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

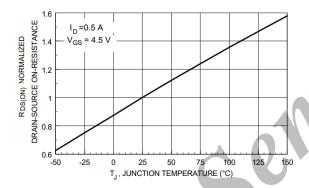


Figure 3. On-Resistance Variation with Temperature.

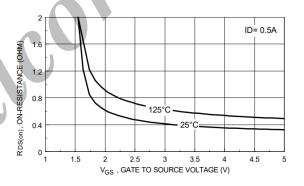


Figure 4. On Resistance Variation with Gate-To- Source Voltage.

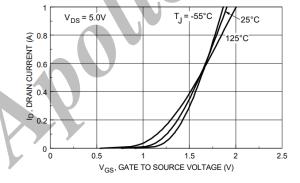


Figure 5. Transfer Characteristics.

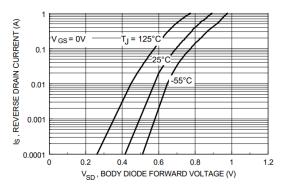


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.



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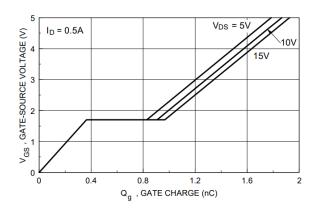


Figure 7. Gate Charge Characteristics.

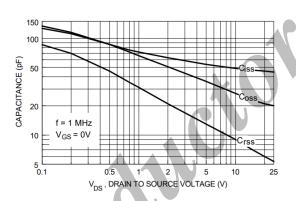


Figure 8. Capacitance Characteristics.

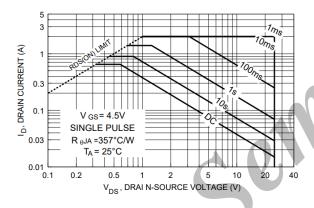


Figure 9. Maximum Safe Operating Area.

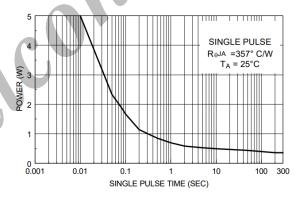


Figure 10. Single Pulse Maximum Power Dissipation.

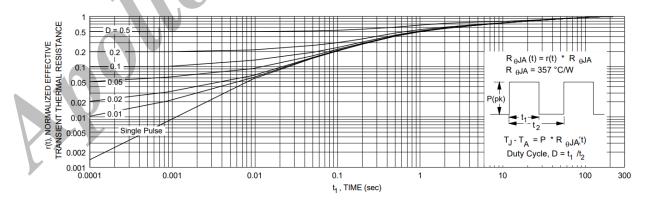


Figure 11. Transient Thermal Response Curve.



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